

SPEC SHEET (FOR REFERENCE)

SHEET No.

G05015A

Rev.

0

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TYPE:6PT1203N1T

CHIP SIZE 0.85 \* 0.65mm

WAFER SIZE 6 inch

Maximum Ratings (Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-Source voltage	VDSS	30	V
Gate-Source voltage	VGSS	±8	V

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			±1	uA	VGS=±8V, VDS=0V
2	IDSS			500	nA	VDS=30V, VGS=0V
3	BVDSS	33			V	ID=100μA, VGS=0V
4	Vth	0.53		1	V	ID=1mA, VDS=10V
5	RDS(on)1		85	120	mΩ	ID=0.5A, VGS=4.5V
6	RDS(on)2		115	160	mΩ	ID=0.5A, VGS=2.5V
7	RDS(on)3		200	260	mΩ	ID=0.1A, VGS=1.5V
8	VSD		0.8	1.1	V	IS=0.5A, VGS=0V
9	Yfs		5		S	VDS=10V, ID=0.5A

※Built in ZD between Gate and Source

PHENITEC SEMICONDUCTOR Corp.